



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Appl. No. : 10/815,840
Applicant : Siegfried Schwarzl
Filed : April 2, 2004
TC/A.U. : 2818
Examiner : LE, Thong Quoc
Confirmation No. : 9682
Docket No. : 0928.0050C
Customer No. : 27896
Title : Semiconductor Memory Having Mutually Crossing
Word and Bit Lines, at which Magnetoresistive
Memory Cells are Arranged

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

TRANSMITTAL OF RESPONSE

Enclosed are the following documents in response to the Office Action mailed November 10, 2004 for the above-identified application:

- ☒ Amendment (11 Pages)
- ☐ Petition for Extension of Time
- ☐ Request for Approval of Drawing Changes
- ☐ Information Disclosure Statement
- ☐ Notice of Appeal
- ☐ Associate Power
- ☐ Revocation and New Power
- ☐ Change of Address
- ☐ Return receipt postcard
- ☒ Other: Check No. 8449 in the amount of \$350.00 for payment of the excess claim fee


The fee has been calculated as follows:

	NO. OF CLAIMS REMAINING AFTER AMENDMENT	NO. OF CLAIMS PREVIOUSLY PAID FOR	EXTRA CLAIMS	RATE	FEE
Total Claims	32	- 29=	3	x \$50.00	\$150.00
Independent Claims	4	- 3 =	1	x \$200.00	\$200.00
If multiple dependent claims are presented, add \$360.00					
Total Amendment Fee					\$0.00
<input type="checkbox"/> Applicant claims Small Entity Status (subtract 50% of Total Application Fee)					
Other fees:					
TOTAL FEE DUE					\$350.00

- ☒ Check No. 8449 the amount of \$350.00 for the total fee as calculated above.
- ☐ Please charge \$ _____ to Deposit Account No. 05-0460 for the total fee. This paper is being submitted in duplicate.
- ☒ The Commissioner is hereby authorized to charge any additional appropriate fees that may be required by this paper, and to credit any overpayment, to Deposit Account No. 05-0460.

Dated: 2/10/05

EDELL, SHAPIRO & FINNAN, LLC
CUSTOMER NO. 27896
 1901 Research Boulevard, Suite 400
 Rockville, MD 20850
 (301) 424-3640

Respectfully submitted by
EDELL, SHAPIRO & FINNAN, LLC

 By: _____
 Heather Morin
 Reg. No. 37,336



AMENDMENT IN RESPONSE TO OFFICE ACTION DATED NOVEMBER 10, 2004
U.S. PATENT APPLICATION NO. 10/815,840 TO SCHWARZL

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AMENDMENT

Sir:

In response to the Office Action mailed November 10, 2004, please amend the above-identified application as follows:

Amendments to the Claims are reflected in the listing of claims, which begins on page 2 of this paper.

Remarks begin on page 10 of this paper.

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